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DATE MAILED: 06/25/2004

APPLICATION NO.	FI	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/634,249	08/04/2003		Dae-Young Kim	51876P356	7777
8791	7590	06/25/2004		EXAMINER	
		OFF TAYLOR &	PHAM, HOAI V		
12400 WILSHIRE BOULEVARD, SEVENTH FLOOR LOS ANGELES, CA 90025				ART UNIT	PAPER NUMBER
2001111023	200.11.02220, 0.1. 70020			2814	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	10/634,249	KIM, DAE-YOUNG				
Office Action Summary	Examiner	Art Unit				
	Hoai V Pham	2814				
The MAILING DATE of this communication Period for Reply	n appears on the cover sheet v	vith the correspondence address				
A SHORTENED STATUTORY PERIOD FOR R THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 Clafter SIX (6) MONTHS from the mailing date of this communication - If the period for reply specified above is less than thirty (30) days, - If NO period for reply is specified above, the maximum statutory properties of the second state of the	ON. FR 1.136(a). In no event, however, may a on. a reply within the statutory minimum of the period will apply and will expire SIX (6) MC statute, cause the application to become A	reply be timely filed irty (30) days will be considered timely. NTHS from the mailing date of this communication. NBANDONED (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on	04 August 2003.					
2a) ☐ This action is FINAL . 2b) ☑	This action is non-final.					
•	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
4) Claim(s) 1-6 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5) Claim(s) is/are allowed. 6) Claim(s) 1-6 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or election requirement.						
Application Papers						
9)⊠ The specification is objected to by the Exa	miner.					
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.						
Applicant may not request that any objection t						
Replacement drawing sheet(s) including the c						
Priority under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-943) Information Disclosure Statement(s) (PTO-1449 or PTO/842) Paper No(s)/Mail Date 04 August 2003.	Paper N	v Summary (PTO-413) o(s)/Mail Date f Informal Patent Application (PTO-152) 				

DETAILED ACTION

Specification

1. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

Claim Rejections - 35 USC § 112

2. Claims 1-6 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 1, the phrase "forming a source and a drain doped with a first conductivity type in an active area on both sides of each word line by an isolation layer of a second conductivity type doped substrate" renders the claim indefinite. It is not clear how "a source and a drain doped with a first conductivity type in an active area on both sides of each word line" can be formed by "an isolation layer of a second conductivity type doped substrate". It is not clear where to form each word line. It is not clear how an isolation layer can have a second conductivity type. Is "an isolation layer" in line 5 the same with "isolation layers" in line 9? Is the "source" doped with both a first conductivity type (lines 3-4) and a second conductivity type (lines 12-13)?

The phrase "an interval which is wider in the source than in the drain" renders the claim indefinite. The scope of the claim can not be defined. It is not clear what "an interval which is wider in the source than in the drain" means.

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Claim 3, line 2, "a twist" should be changed to --the tilt angle--.

Claim 4, the phrase "the tilt ion implantation process carried out in a direction perpendicular to the word line" renders the claim indefinite. It is not clear how the tilt ion implantation can be perpendicular to the word line.

Claim 6, line 1, delete "of fabricating the semiconductor device".

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

4. Claims 1-6, insofar as clear, are rejected under 35 U.S.C. 102(b) as being anticipated by Krivokapic et al. [U.S. Pat. 6,008,094].

Krivokapic et al. (figs. 4-5, cols. 4-5) discloses a method of fabricating a semiconductor device, comprising the step of:

forming a gate electrode (16) on a substrate;

forming an isolation layer (19) on the gate electrode and the substrate, wherein the isolation layer having an expose portion on a source region;

implanting boron into the source region by using the isolation layer (19) as an ion implanting mask during a tilt ion implantation process, wherein the tilt ion implantation process is carried out using a tilt angle of about 7° to 25°.

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Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hoai V Pham whose telephone number is 571-272-1715. The examiner can normally be reached on 9:30A.M. - 8:00P.M..

- 6. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M. Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.
- 7. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hoai Pham June 11, 2004